Preferred Device

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

Features

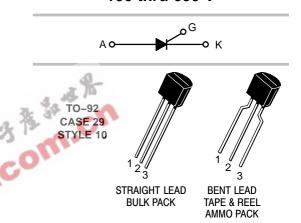
- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 V
- On-State Current Rating of 0.8 A RMS at 80°C
- High Surge Current Capability 10 A
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to $dV/dt 20 V/\mu sec$ Minimum at $110^{\circ}C$
- Glass-Passivated Surface for Reliability and Uniformity
- Pb–Free Packages are Available*



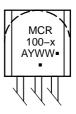
ON Semiconductor®

http://onsemi.com

SCRs 0.8 A RMS 100 thru 600 V



MARKING DIAGRAM



- x = Specific Device Code
- A = Assembly Location
- = Year
- WW = Work Week

= Pb–Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT				
1	Cathode			
2	Gate			
3	Anode			

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

Preferred devices are recommended choices for future use

and best overall value.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off–State Voltage (Notes 1 and 2) (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz; Gate Open) MCR100-3 MCR100-4 MCR100-6 MCR100-8	V _{drm,} V _{rrm}	100 200 400 600	V	
On-State RMS Current, (T _C = 80°C) 180° Conduction Angles	I _{T(RMS)}	0.8	А	
Peak Non-Repetitive Surge Current, (1/2 Cycle, Sine Wave, 60 Hz, $T_J = 25^{\circ}C$)	I _{TSM}	10	А	
Circuit Fusing Consideration, (t = 8.3 ms)	l ² t	0.415	A ² s	
Forward Peak Gate Power, (T _A = 25°C, Pulse Width $\leq 1.0 \ \mu$ s)	P _{GM}	0.1	W	
Forward Average Gate Power, ($T_A = 25^{\circ}C$, t = 8.3 ms)	P _{G(AV)}	0.10	W	
Forward Peak Gate Current, (T _A = 25°C, Pulse Width $\leq 1.0 \ \mu$ s)	I _{GM}	1.0	А	
Reverse Peak Gate Voltage, (T _A = 25°C, Pulse Width \leq 1.0 µs)	V _{GRM}	5.0	V	
Operating Junction Temperature Range @ Rate V_{RRM} and V_{DRM}	TJ	-40 to 110	°C	
Storage Temperature Range	T _{stg}	-40 to 150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

2. See ordering information for exact device number options.

THERMAL CHARACTERISTICS

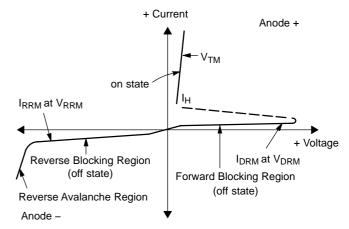
Characteristic			Syml	loc	Max		Unit	
Thermal Resistance, Junction-to-Case Junction-to-Ambient			$R_{ extsf{ heta}JC}$ $R_{ extsf{ heta}JA}$		75 200	c	°C/W	
Lead Solder Temperature (<1/16" from case, 10 secs max)			ΤL		260		°C	
ELECTRICAL CHARACTERISTICS (T _C = 25°C unle	ess otherwise noted)						
Characteristic		Sym	bol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS								
Peak Repetitive Forward or Reverse Blocking Current ($V_D = Rated V_{DRM}$ and V_{RRM} ; $R_{GK} = 1 k\Omega$)	Note 2) T _C = 25°C T _C = 110°C	I _{DRM} ,	I _{RRM}	_	-	10 100	μΑ	
ON CHARACTERISTICS						100		
Peak Forward On–State Voltage [*] ($I_{TM} = 1.0 \text{ A Peak} @ T_A = 25^{\circ}\text{C}$)		V _T	М	-	-	1.7	V	
Gate Trigger Current (Continuous dc) (Note 3) $(V_{AK} = 7.0 \text{ Vdc}, R_L = 100 \Omega)$	$T_{C} = 25^{\circ}C$	I _G	Т	-	40	200	μΑ	
Holding Current ⁽²⁾ (V _{AK} = 7.0 Vdc, Initiating Current = 20 mA)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	۱۲	ł		0.5 -	5.0 10	mA	
Latch Current $(V_{AK} = 7.0 \text{ V}, \text{ Ig} = 200 \mu\text{A})$	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	١	-		0.6 -	10 15	mA	
Gate Trigger Voltage (Continuous dc) (Note 3) (V_{AK} = 7.0 Vdc, R_L = 100 Ω) T_C = -40°C	$T_{C} = 25^{\circ}C$	VG	ĞΤ		0.62	0.8 1.2	V	
DYNAMIC CHARACTERISTICS	-						-	
Critical Rate of Rise of Off–State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform, R_{GK} = 10$	00 Ω,T _J = 110°C)	dV	/dt	20	35	-	V/μs	
Critical Rate of Rise of On–State Current (I _{PK} = 20 A; Pw = 10 µsec; diG/dt = 1 A/µsec, Igt = 20) mA)	di/	dt	-	-	50	A/µs	

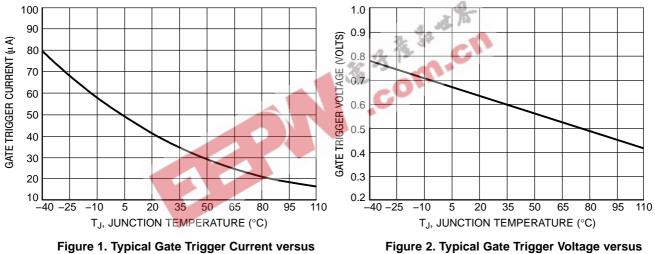
*Indicates Pulse Test: Pulse Width \leq 1.0 ms, Duty Cycle \leq 1%.

3. $R_{GK} = 1000 \Omega$ included in measurement. 4. Does not include R_{GK} in measurement.

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Peak on State Voltage
Ι _Η	Holding Current





Junction Temperature

Junction Temperature

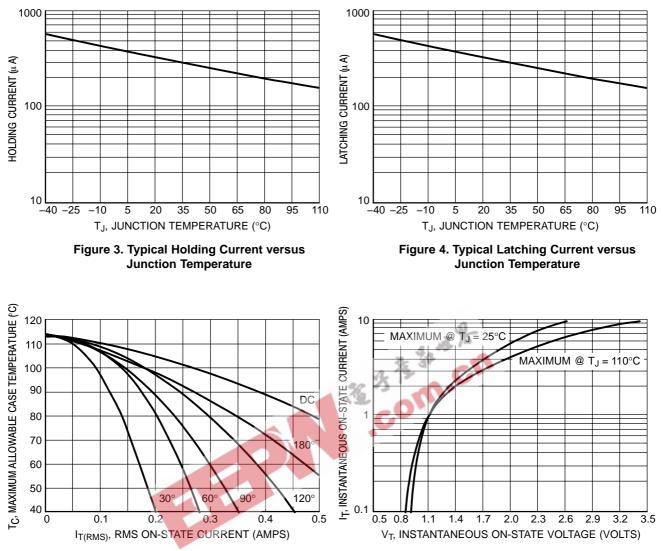


Figure 5. Typical RMS Current Derating

Figure 6. Typical On–State Characteristics

ORDERING INFORMATION

Device	Package Code	Shipping [†]			
MCR100-003					
MCR100-004		5000 Helite / Deve			
MCR100-006		5000 Units / Box			
MCR100-008					
MCR100-3RL					
MCR100-6RL	TO-92 (TO-226)	2000 / Tape & Reel			
MCR100-6RLRA					
MCR100-6RLRM					
MCR100-6ZL1		2000 / Tape & Ammo Pack			
MCR100-8RL		2000 / Tape & Reel			
MCR100-3G					
MCR100-4G					
MCR100-6G		5000 Units / Box			
MCR100-8G		4			
MCR100-3RLG	TO-92 (TO-226)	2000 / Tape & Reel			
MCR100-6RLG	(Pb-Free)	2000 / Tape & Reel			
MCR100-6RLRAG	3	3			
MCR100-6RLRMG					
MCR100-6ZL1G		2000 / Tape & Ammo Pack			
MCR100-8RLG		2000 / Tape & Reel			

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TO-92 EIA RADIAL TAPE IN BOX OR ON REEL

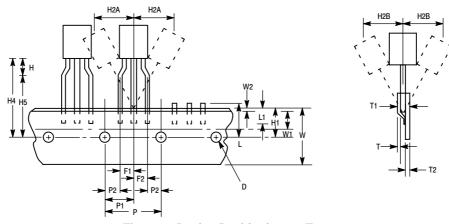


Figure 7. Device Positioning on Tape

	ool Item		Specification				
			Inches		Millimeter		
Symbol			Max	Min	Max		
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2		
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51		
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8		
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0		
H1	Feedhole Location	0.3346	0.3741	8.5	9.5		
H2A	Deflection Left or Right	0	0.039	0	1.0		
H2B	Deflection Front or Rear	0	0.051	0	1.0		
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5		
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5		
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11		
L1	Lead Wire Enclosure	0.09842	_	2.5	—		
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9		
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75		
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95		
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20		
T1	Overall Taped Package Thickness	—	0.0567	—	1.44		
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65		
W	Carrier Strip Width	0.6889	0.7481	17.5	19		
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3		
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5		

NOTES:

1. Maximum alignment deviation between leads not to be greater than 0.2 mm.

Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
Component lead to tape adhesion must meet the pull test requirements.

4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.

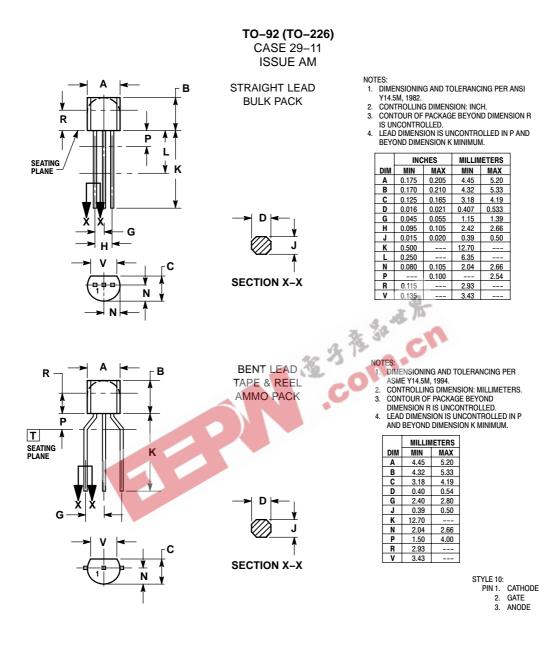
5. Hold down tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.

6. No more than 1 consecutive missing component is permitted.

7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.

8. Splices will not interfere with the sprocket feed holes.

PACKAGE DIMENSIONS



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